Topics

- Low Power Techniques

Based on Penn State CSE477 Lecture Notes ©2002 M.J. Irwin and adapted from *Digital Integrated Circuits* ©2002 J. Rabaey

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Review: Energy & Power Equations $\mathbf{E} = \mathbf{C}_{||} \mathbf{V}_{DD}^{2} \mathbf{P}_{0 \rightarrow 1} + \mathbf{t}_{sc} \mathbf{V}_{DD} \mathbf{I}_{peak} \mathbf{P}_{0 \rightarrow 1} + \mathbf{V}_{DD} \mathbf{I}_{leakage}$ $f_{0 \rightarrow 1} = P_{0 \rightarrow 1} * f_{clock}$ $\mathbf{P} = \mathbf{C}_{\mathsf{L}} \, V_{\mathsf{DD}}^2 \, \mathbf{f}_{0 \to 1} + \mathbf{t}_{\mathsf{sc}} \mathbf{V}_{\mathsf{DD}} \, \mathbf{I}_{\mathsf{peak}} \, \mathbf{f}_{0 \to 1} + \mathbf{V}_{\mathsf{DD}} \, \mathbf{I}_{\mathsf{leakage}}$ Short-circuit Leakage power Dynamic power (~90% today and (~2% today and power decreasing (~8% today and increasing) relatively) decreasing

absolutely)

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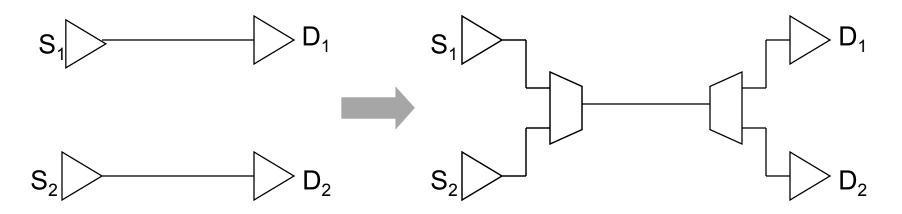
Power and Energy Design Space

	Constant Throughput/Latency		Variable Throughput/Latency	
Energy	Design Time	Non-active Modules		Run Time
Active	Logic Design Reduced V _{dd} Sizing	Clock Gating Sleep Transistors		DFS, DVS (Dynamic Freq, Voltage Scaling)
	Multi-V _{dd}			- Coamigy
Leakage	+ Multi-V _T	Multi- Variab		+ Variable V_T

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Bus Multiplexing

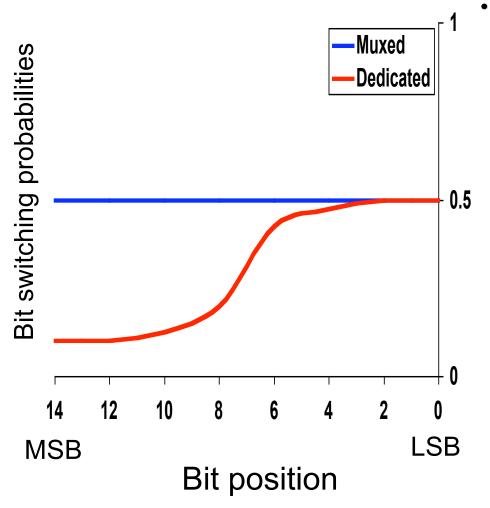
- Buses are a significant source of power dissipation due to high switching activities and large capacitive loading
 - 15% of total power in Alpha 21064
 - 30% of total power in Intel 80386
- Share long data buses with time multiplexing (S₁ uses even cycles, S₂ odd)



• But what if data samples are correlated (e.g., sign bits)?

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Correlated Data Streams

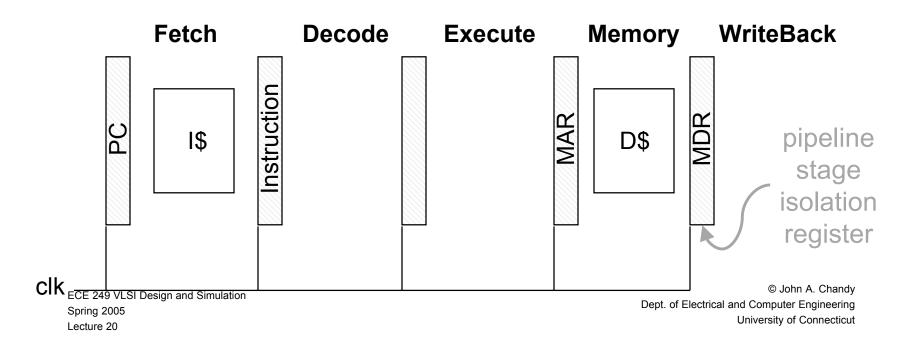


- For a shared (multiplexed) bus advantages of data correlation are lost (bus carries samples from two uncorrelated data streams)
 - Bus sharing should not be used for positively correlated data streams
 - Bus sharing may prove advantageous in a negatively correlated data stream (where successive samples switch sign bits) more random switching

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Glitch Reduction by Pipelining

- Glitches depend on the logic depth of the circuit gates deeper in the logic network are more prone to glitching
 - arrival times of the gate inputs are more spread due to delay imbalances
 - usually affected more by primary input switching
- Reduce logic depth by adding pipeline registers
 - additional energy used by the clock and pipeline registers



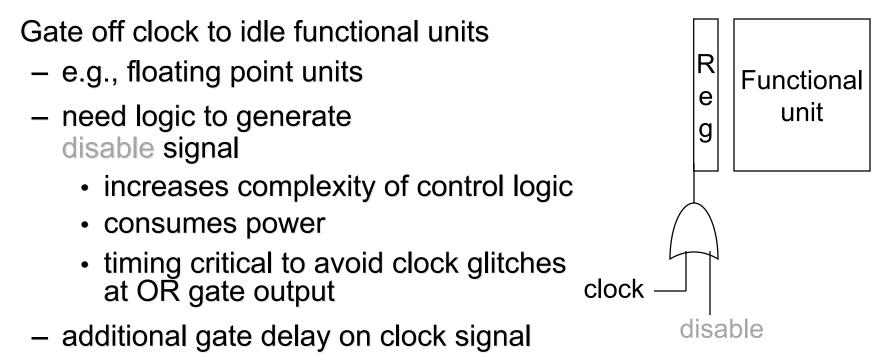
Power and Energy Design Space

	Constant Throughput/Latency		Variable Throughput/Latency	
Energy	Design Time	Non-active Modules		Run Time
	Logic Design	Clock Gating		DFS, DVS (Dynamic
Active	Reduced V_{dd}			
	Sizing			Freq, Voltage
	Multi-V _{dd}			Scaling)
		Sleep Transistors Multi-V _{dd} Variable V _T		+ Variable V_{T}
Leakage	+ Multi-V _⊤			

Clock Gating

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 Most popular method for power reduction of clock signals and functional units

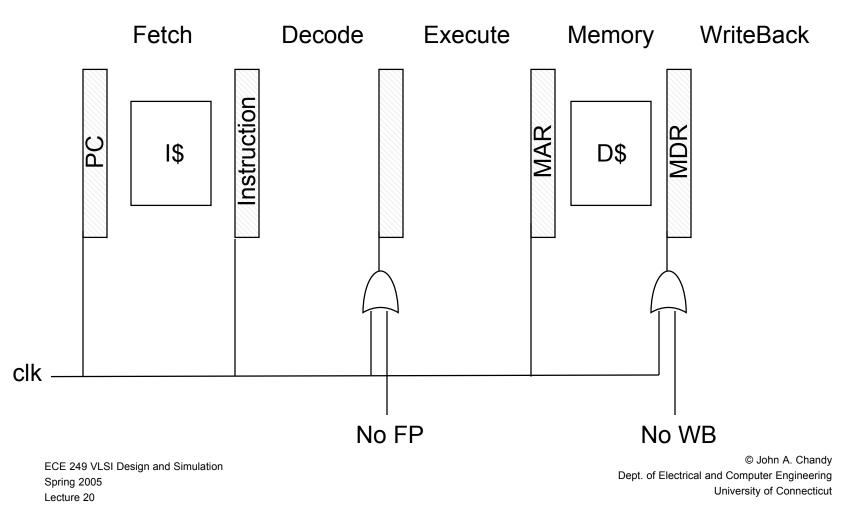


 gating OR gate can replace a buffer in the clock distribution tree

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Clock Gating in a Pipelined Datapath

• For idle units (e.g., floating point units in Exec stage, WB stage for instructions with no write back operation)

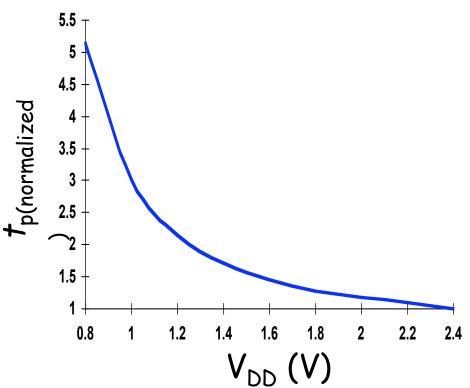


Power and Energy Design Space

	Constant Throughput/Latency		Variable Throughput/Latency	
Energy	Design Time	Non-active Modules		Run Time
	Logic Design	Clock Gating		DFS, DVS
Active	Reduced V_{dd}			(Dynamic
	Sizing			Freq, Voltage
	Multi-V _{dd}			Scaling)
		Sleep Transistors		
Leakage	+ Multi-V _⊤	Multi	-V _{dd}	+ Variable V_T
		Variable V_T		

Review: Dynamic Power as a Function of V_{DD}

- Decreasing the V_{DD} decreases dynamic energy consumption (quadratically)
- But, increases gate delay (decreases performance)



 Determine the critical path(s) at design time and use high V_{DD} for the transistors on those paths for speed. Use a lower V_{DD} on the other logic to reduce dynamic energy consumption.

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Dynamic Frequency and Voltage Scaling

- Intel's SpeedStep
 - Hardware that steps down the clock frequency (dynamic frequency scaling – DFS) when the user unplugs from AC power
 - PLL from 650MHz \rightarrow 500MHz
 - CPU stalls during SpeedStep adjustment

Dynamic Frequency and Voltage Scaling

- Transmeta LongRun
 - Hardware that applies both DFS and DVS (dynamic supply voltage scaling)
 - 32 levels of V_{DD} from 1.1V to 1.6V
 - PLL from 200MHz \rightarrow 700MHz in increments of 33MHz
 - Triggered when CPU load change is detected by software
 - heavier load \rightarrow ramp up V_{DD}, when stable speed up clock
 - lighter load \rightarrow slow down clock, when PLL locks onto new rate, ramp down V_{DD}
 - CPU stalls only during PLL relock (< 20 microsec)

Dynamic Thermal Management (DTM)



Trigger Mechanism: When do we enable DTM techniques? Initiation Mechanism: How do we enable technique?



Response Mechanism:

What technique do we enable?

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DTM Trigger Mechanisms



- Mechanism: How to deduce temperature?
- Direct approach: on-chip temperature sensors
 - Based on differential voltage change across 2 diodes of different sizes
 - May require >1 sensor
 - Hysteresis and delay are problems

- Policy: When to begin responding?
 - Trigger level set too high means higher packaging costs
 - Trigger level set too low means frequent triggering and loss in performance
- Choose trigger level to exploit difference between average and worst case power_{© John A. Chandy}

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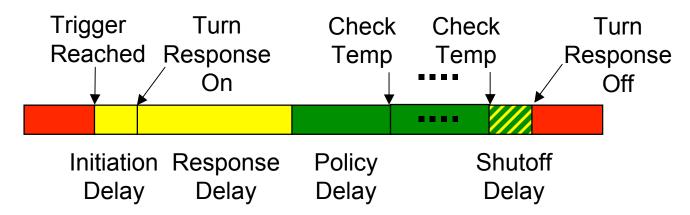
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DTM Initiation and Response Mechanisms



- Operating system or microarchitectural control?
 - Hardware support can reduce performance penalty by 20-30%
- Initiation of policy incurs some delay
 - When using DVS and/or DFS, much of the performance penalty can be attributed to enabling/disabling overhead
 - Increasing policy delay reduces overhead; smarter initiation techniques would help as well
- Thermal window (100Kcycles+)
 - Larger thermal windows "smooth" short thermal spikes

DTM Activation and Deactivation Cycle

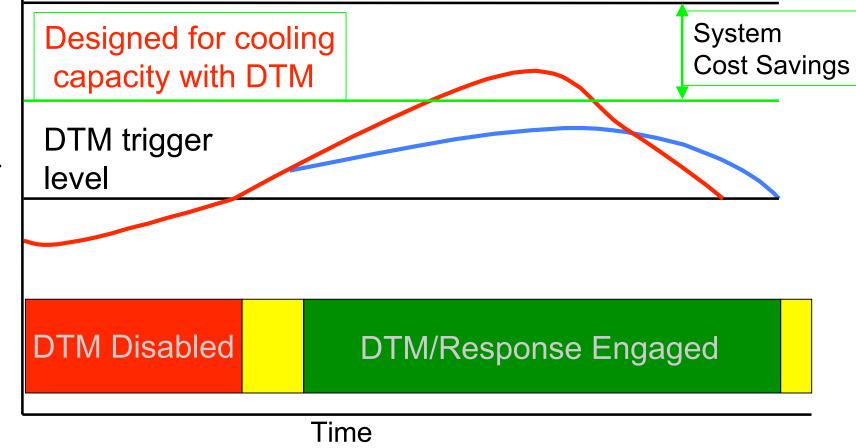


- □ Initiation Delay OS interrupt/handler
- Response Delay Invocation time (e.g., adjust clock)
- Policy Delay Number of cycles engaged
- Shutoff Delay Disabling time (e.g., re-adjust clock)

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DTM Savings Benefits

Designed for cooling capacity without DTM



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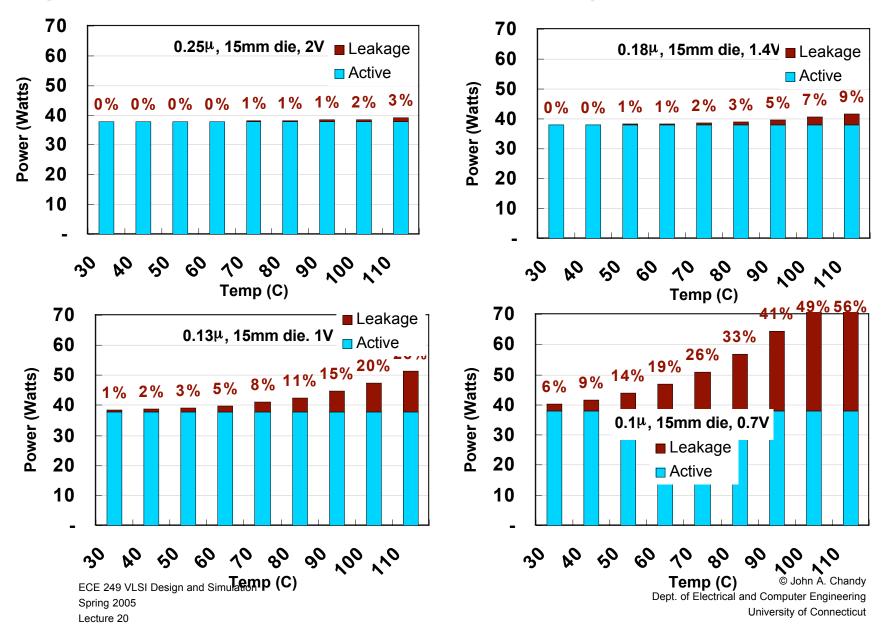
Temperature

Power and Energy Design Space

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		Sleep Tra	Insistors	
Leakage	+ Multi-V _T	Multi-V _{dd}		+ Variable V_T
		Variab	le V _T	

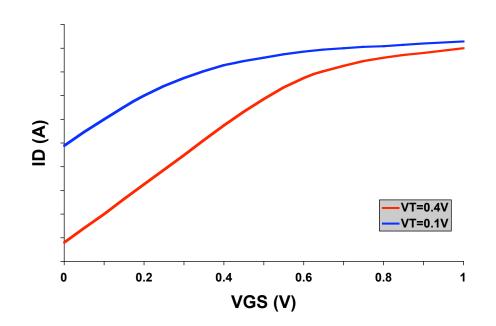
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Speculated Power of a 15mm μ P



Review: Leakage as a Function of Design Time V_{T}

- Reducing the V_T increases the subthreshold leakage current (exponentially)
- But, reducing V_T decreases gate delay (increases performance)



Determine the critical path(s) at design time and use low V_T devices on the transistors on those paths for speed.
Use a high V_T on the other logic for leakage control.

Review: Variable V_T (ABB) at Run Time

 $V_T = V_{T0} + \gamma \left(\sqrt{\left| -2\phi_F + V_{SB} \right|} - \sqrt{\left| -2\phi_F \right|} \right)$

where V_{T0} is the threshold voltage at V_{SB} = 0

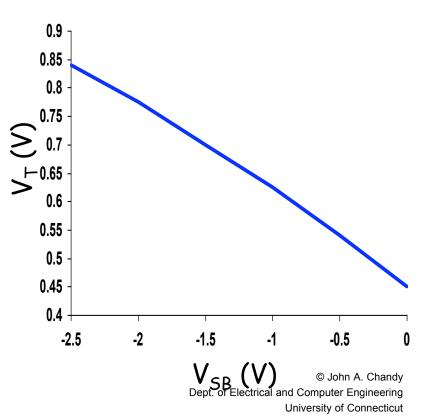
 V_{SB} is the source-bulk (substrate) voltage

 γ is the body-effect coefficient

For an n-channel device,
the substrate is normally tied
to ground

 □ A negative bias causes V_T to increase from 0.45V to 0.85V

Adjusting the substrate bias at run time is called adaptive body-biasing (ABB)



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Next class

- Testing and Verification
- Exam April 12th
- No lab tomorrow
 - Work on final project